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Dynamics of optical gain in In$_x$Ga$_{1-x}$N multi-quantum-well-based laser diodes

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Dynamical behavior of optical gain formation has been assessed at room temperature in the In$_x$Ga$_{1-x}$N multi-quantum-well (MQW) based laser diodes (LDs) by employing pump and probe spectroscopy with a pulse width of 150 fs. The LDs are composed of (a) In$_{0.01}$Ga$_{0.99}$N−In$_{0.02}$Ga$_{0.98}$N MQW and (b) In$_{0.3}$Ga$_{0.7}$N−In$_{0.05}$Ga$_{0.95}$N MQW, whose stimulated emissions correspond to near ultraviolet (390 nm) and blue (440 nm), respectively. The optical gain was contributed from the nearly delocalized states [the lowest-quantized MQW levels (LQL)] in the sample (a), while it was from highly localized levels with respect to the LQL by 500 meV for the sample (b). It was found that the photogenerated carriers rapidly (less than 1 ps) transferred to the LQL, and then relaxed to the localized tail within the time scale of about 5 ps, giving rise to the optical gain. Such gain spectra were saturated and other bands appeared in the vicinity of the LQL under higher photoexcitation.

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of the pump beam. The whole measurements have been done at RT.

In the pump and probe spectroscopy, the transmission spectrum of the probe beam detected in the presence of the pump beam \((T + \Delta T)\) is compared to the spectrum without the pump beam \((T)\), giving the frequency \((\omega)\)-dependent \(\Delta T(\omega, I_{ex}, t_d)\) of the sample for different intensities of the pump \((I_{ex})\), and for different time delays after the pulsed pumping \((t_d)\). The photoinduced change of optical density \([\Delta OD(\omega, I_{ex}, t_d)]\)

\[
\Delta OD = \log \left( \frac{T}{T + \Delta T} \right) = \Delta \alpha d \times 0.434, \tag{1}
\]

where \(\Delta \alpha(\omega, I_{ex}, t_d)\) is the photoinduced change of absorption coefficient and \(d\) is the thickness of absorbing layer.

Figure 1 shows time-integrated photoluminescence (TI-PL) spectra under photoexcitation energy density \((I_{ex})\) of 100 \(\text{J/cm}^2\) taken at two types of LDs. Absorption spectra under low photoexcitation (Xe lamp) corresponding to the density of states are also depicted in Fig. 1. The lowest quantized energy levels within the wells (designated as \(E_{ex1hh}\)) were estimated by reflectroreflectance spectroscopy. In contrast to sample (a), the PL of sample (b) is composed of two emission bands, and the main bands are located on the low-energy side with respect to \(E_{ex1hh}\) by 500 meV. Blueshift of these bands under increased \(I_{ex}\) conditions (from 10 \(\text{J/cm}^2\) to 20 \(\mu\text{J/cm}^2\)) is about a few tens meV, which is substantially smaller that the energy difference. These phenomena were attributed to the localization of excitons whose origin is probably due to In-rich quantum dot (QD) like centers. This model is supported by the energy-dispersive x-ray microanalysis using scanning transmission electron microscopy. Moreover, the zero-dimensional feature of excitons is revealed especially in blue-emitting quantum wells (QWs) where almost no temperature dependence of the radiative lifetime was observed from cryogenic temperature to RT.

The TI-PL spectra were detected with the edge geometry from the resonator cavity—the length of which was about 1 mm. As shown in Figs. 2 and 3, stimulated emission (SE) was observed from every sample if \(I_{ex}\) is more than about 50 \(\mu\text{J/cm}^2\). SE appears on the low-energy side of the spontaneous emission (SPE) by 32 meV for sample (a), while from the high-energy side of the main SPE band by 130 meV for sample (b). The Large blueshift in sample (b) may be due to the band-filling effects within localized states, and/or due to the screening effect of the internal electric field. Nevertheless, this energy is still substantially smaller than the localization energy (500 meV) observed in the SPE. Therefore, it is probable that the optical gain was contributed from the localized centers for the blue LD mean-In composition in which the wells is about 30%. However, as shown in Fig. 3(b), these SE bands are saturated if \(I_{ex}\) is more than about 100 \(\mu\text{J/cm}^2\), then new SE bands grow on the low-energy side of the SPE bands originating from the \(E_{ex1hh}\) transition.

The dynamical behavior of dense carriers was characterized by measurement of the differential absorption coefficient by employing pump and probe spectroscopy. Figure 4(a) shows the variation of differential optical density spectra as a function of time after pumping at 370 nm under \(I_{ex} = 200 \mu\text{J/cm}^2\) in sample (a) (In\(_{0.2}\)Ga\(_{0.8}\)N QW, near-UV LD). The optical density spectrum taken under the low \(I_{ex}\) condition is depicted as a reference. PL spectra of both SE (\(I_{ex} = 200 \mu\text{J/cm}^2\)) and SPE (\(I_{ex} = 100 \text{J/cm}^2\)) are also shown in Fig. 4(a). The sheet carrier density is roughly estimated to be \(1.9 \times 10^{13} \text{cm}^{-2}\) under \(I_{ex} = 200 \mu\text{J/cm}^2\). At the initial stage of excitation \((t = 0)\)
bleaching of the photoabsorption was observed in the vicinity of the pumping energy. However, the negative peak of \( \Delta OD \) rapidly reached the level of \( E_{\text{ex1hh}} \), at a time scale of less than 1 ps. The red shift of \( E_{\text{ex1hh}} \) was observed with increasing time (13 meV at \( t = 200 \, \text{ps} \)), probably because screening of the piezoelectric field is reduced with decreasing carrier density. Optical gain was generated on the low-energy side of the negative peak due to the effect of band-gap renormalization. As shown in Fig. 4(b), maximum optical gain as large as about 8000 cm\(^{-1} \) was reached at \( t = 2 \, \text{ps} \).

The dynamics of dense carriers was also assessed for sample (b) (blue LD), as shown in Fig. 5(a). The tail of differential absorption began to grow toward the bottom of the localized levels just after the bleaching at \( E_{\text{ex1hh}} \) is completed. The time scale for reaching to the bottom was about 5 ps. Therefore, it was found that photogenerated carriers and/or excitons efficiently transfer to deeply localized levels without the effect of a phonon bottleneck observed in other QD systems. As described before, stimulated emission originating from localized centers [designated as SE\(_2 \) in Fig. 5(a)] saturates under higher photoexcitation, and a new SE from \( E_{\text{ex1hh}} \) (SE\(_2 \)) appears in these samples. Figure 5(b) shows the dynamics of optical gain spectra under \( I_{\text{ex}} = 200 \, \text{µJ/cm}^2 \) taken at sample (b) (blue LD). SE\(_2 \) began to grow at \( t = 1-2 \, \text{ps} \) and reached the maximum \( (g = 3000 \, \text{cm}^{-1}) \) at \( t = 4 \, \text{ps} \), while the temporal behavior of SE\(_1 \) is delayed by about 2 ps with respect to that of SE\(_2 \).

In conclusion, the dynamics of dense carriers has been studied at RT in (a) In\(_{0.1}\)Ga\(_{0.9}\)N/In\(_{0.02}\)Ga\(_{0.98}\)N and (b) In\(_{0.3}\)Ga\(_{0.7}\)N/In\(_{0.05}\)Ga\(_{0.95}\)N MQW LD structures by means of pump and probe spectroscopy. The optical gain was contributed from the nearly delocalized state of the QW \( (E_{\text{ex1hh}}) \) in sample (a). However, it was generated from both QD-like localized centers and the QW under moderately high photoexcitation in sample (b). It was found that the photogenerated carriers rapidly (less than 1 ps) transferred to the LQL, and then relaxed to the localized tail within the time scale of several ps, giving rise to the optical gain.

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